

MAC6068C-MAC6075C

High-reliability discrete products and engineering services since 1977

SILICON BIDIRECTIONAL THYRISTORS

FEATURES

- Available as "HR" (high reliability) screened per MIL-PRF-19500, JANTX level. Add "HR" suffix to base part number.
- Available as non-RoHS (Sn/Pb plating), standard, and as RoHS by adding "-PBF" suffix.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Peak repetitive off-state voltage ⁽¹⁾			
(T _j = 110°C)			
MAC6068C		25	
MAC6069C		50	
MAC6070C	V _{DRM}	100	Volts
MAC6071C		200	
MAC6073C		400	
MAC6074C		500	
MAC6075C		600	
RMS on-state current ($T_c = 85^{\circ}C$)	I _{T(RMS)}	4.0	Amps
Peak non-repetitive surge current			A
(1 cycle, 60 Hz, T _J = -40 to +110°C)	I _{TSM}	30	Amps
Circuit fusing considerations (T _J = -40 to +110°C, t = 1.0 to 8.3ms)	l ² t	3.6	A ² s
Peak gate power	P _{GM}	10	Watts
Average gate power	P _{G(AV)}	0.5	Watts
Operating junction temperature range	T,	-40 to +110	°C
Storage temperature range	T _{stg}	-40 to +150	°C
Mounting torque (6-32 screw) ⁽²⁾		8.0	In. lb.

Note 1: Ratings apply for open gate conditions. Thyristor devices shall not be tested with a constant current source for blocking capability such that the voltage applied exceeds the rated

blocking voltage.

Note 2: Torque rating applies with use of torque washer. Mounting torque in excess of 6 in. lb. does not appreciably lower case to sink thermal resistance. Main terminal 2 and heatsink contact pad are common.

Soldering temperatures shall not exceed 200°C for 10 seconds.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Maximum	Unit
Thermal resistance, junction to case	R _{ejc}	3.5	°C/W
Thermal resistance, junction to ambient	R _{eja}	60	°C/W

ELECTRICAL CHARACTERISTICS (T_c = 25°C and either polarity of MT2 to MT1 voltage, unless otherwise noted)

Characteristic	Symbol	Min	Тур.	Max	Unit
Peak blocking current (either direction)					
(Rated V_{DRM} @ T_J = 125°C, gate open)	DRM	-	-	2.0	mA
Peak on-state voltage (either direction)	V				Volts
(I _{TM} = 6.0A peak)	V _{TM}	-	-	2.0	VOILS
Gate trigger voltage					
$(V_D = 12V, R_L = 100\Omega, T_J = -40^{\circ}C)$					
MT2(+),G(+); MT2(-),G(-), all types		-	1.4	2.5	
MT2(+),G(-); MT2(-),G(+), all types	V _{GT}	-	1.4	2.5	Volts
$(V_D = Rated V_{DRM}, R_L = 10k\Omega, T_J = 110^{\circ}C)$					
MT2(+),G(+); MT2(-),G(-), all types		0.2	-	-	
MT2(+),G(-); MT2(-),G(+), all types		0.2	-	-	



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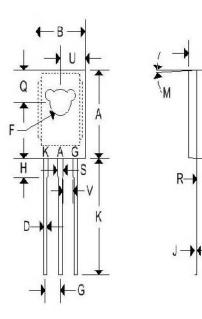
Holding current (either direction)					
$(V_D = 12V, \text{ gate open}, T_J = -40^{\circ}C, \text{ initiating current} = 1A)$					
MAC6068C-MAC6075C	I _H	-	-	30	mA
T _J = 25°C					
MAC6068C-MAC6075C		-	-	15	

		Quadrant			
Characteristic	Symbol	I	Ш	Ш	IV
		mA	mA	mA	mA
Peak gate trigger current					
(Main terminal voltage = 12V, $R_L = 100\Omega$, $T_J = 25^{\circ}C$)	I _{GTM}	10	10	10	20
(Main terminal voltage = 12V, $R_L = 100\Omega$, $T_J = -40^{\circ}C$)		20	20	20	40

MECHANICAL CHARACTERISTICS

Case	TO-126	
Marking	Alpha-numeric	
Pin out:	See below	

-C



		TO	-126		
	Inc	hes	Millimeters		
	Min	Max	Min	Max	
A	0.425	0.435	10.80	11.050	
В	0.295	0.305	7.490	7.750	
С	0.095	0.105	2.410	2.670	
D	0.020	0.026	0.510	0.660	
F	0.115	0.125	2.920	3.180	
G	0.091	0.097	2.310	2.460	
H	0.050	0.095	1.270	2.410	
J	0.015	0.025	0.380	0.640	
K	0.595	0.655	15.110	16.640	
М	3° TYP		3° .	TYΡ	
Q	0.148	0.158	3.760	4.010	
R	0.045	0.055	1.140	1.400	
S	0.025	0.035	0.640	0.890	
U	0.145	0,155	3.680	3.940	
٧	0.040		1.020	1.5%	



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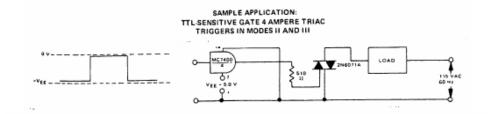


FIGURE 1 - AVERAGE CURRENT DERATING

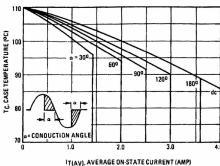
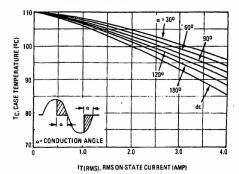
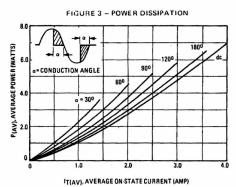
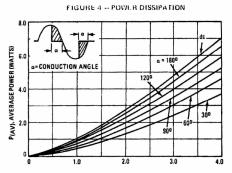


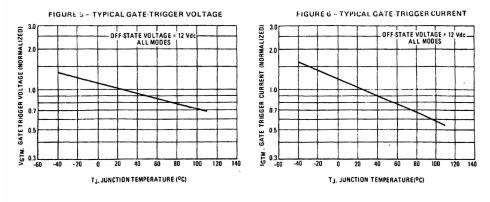
FIGURE 2 - RMS CUERENT DERATING







T(RMS), RMS ON-STATE CURRENT (AMP)



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